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Product Category	MPU/MCU		Document No.	TN-RX*-A051A/E	Rev.	1.00
Title	Changes to Data Hold Time in Electrical Characteristics of Groups RX610, RX62G, RX62N, RX621, RX62T, RX630, RX63N, and RX631		Information Category	Technical Notification		
Applicable Product	RX610 Group, RX62G Group, RX62N Group, RX621 Group, RX62T Group, RX630 Group, RX63N Group, RX631 Group	Lot No. All	Reference Document	RX610 Group User's Manual: Hardware Rev.1.20 (R01UH0032EJ0120) RX62G Group User's Manual: Hardware Rev.1.00 (R01UH0321EJ0100) RX62N Group, RX621 Group User's Manual: Hardware Rev.1.30 (R01UH0033EJ0130) RX62T Group User's Manual: Hardware Rev.1.30 (R01UH0034EJ0130) RX630 Group User's Manual: Hardware Rev.1.50 (R01UH0040EJ0150) RX63N Group, RX631 Group User's Manual: Hardware Rev.1.60 (R01UH0041EJ0160)		

This document describes changes to the data hold time in Electrical Characteristics of RX610, RX62G, RX62N, RX621, RX62T, RX630, RX63N, and RX631 MCUs. Changes are underlined in the list below.

- RX610 Group ROM (Flash Memory for Code Storage) Characteristics

  Refer to Table 29.11 in RX610 Group User's Manual: Hardware Rev.1.20

Before change

ROM (Flash Memory for Code Storage) Characteristics

Conditions: V_{CC} = $PLLV_{CC}$ = AV_{CC} = 3.0 to 3.6 V, V_{REFH} = 3.0 V to AV_{CC}, V_{SS} = $PLLV_{SS}$ = V_{REFL} = 0 V
Operating temperature range during programming/erasing:
T_a = -20 to +85°C (regular specifications), T_a = -40 to +85°C (wide-range specifications)

Item		Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Programming time	256 bytes	t_{P256}	—	2	12	ms	PCLK = 50 MHz
	8 Kbytes	t_{P8K}	—	45	100	ms	N_{PEC} ≤ 100
	256 bytes	t_{P256}	—	2.4	14.4	ms	PCLK = 50 MHz
	8 Kbytes	t_{P8K}	—	54	120	ms	N_{PEC} > 100
Erasure time	8 Kbytes	t_{E8K}	—	50	120	ms	PCLK = 50 MHz
	64 Kbytes	t_{E64K}	—	400	875	ms	N_{PEC} ≤ 100
	128 Kbytes	t_{E128K}	—	800	1750	ms	
	8 Kbytes	t_{E8K}	—	60	144	ms	PCLK = 50 MHz
	64 Kbytes	t_{E64K}	—	480	1050	ms	N_{PEC} > 100
	128 Kbytes	t_{E128K}	—	960	2100	ms	
Rewrite/erase cycle*1		N_{PEC}	1000*2	—	—	Times	
Suspend delay time during writing		t_{SPD}	—	—	120	µs	Figure 29.29
First suspend delay time during erasing (in suspend priority mode)		t_{SESD1}	—	—	120	µs	PCLK = 50 MHz
Second suspend delay time during erasing (in suspend priority mode)		t_{SESD2}	—	—	1.7	ms	
Suspend delay time during erasing (in erasure priority mode)		t_{SEED}	—	—	1.7	ms	
Data hold time*3		T_{DRP}	10	—	—	Year	

Notes: 1. Definition of rewrite/erase cycle:
The rewrite/erase cycle is the number of erasing for each block. When the rewrite/erase cycle is n times (n = 1000), erasing can be performed n times for each block. For instance, when 256-byte writing is performed 32 times for different addresses in 8-Kbyte block and then the entire block is erased, the rewrite/erase cycle is counted as one. However, writing to the same address for several times as one erasing is not enabled (over writing is prohibited).
2. This indicates the minimum number that guarantees the characteristics after rewriting. (The guaranteed value is in the range from one to the minimum number.)
3. This indicates the characteristic when rewrite is performed within the specification range including the minimum number.

After change

ROM (Flash Memory for Code Storage) Characteristics (1)

Conditions: V_{CC} = $PLLV_{CC}$ = AV_{CC} = 3.0 to 3.6 V, V_{REFH} = 3.0 V to AV_{CC}, V_{SS} = $PLLV_{SS}$ = V_{REFL} = 0 V
Operating temperature range during programming/erasing:
T_a = -20 to +85°C (regular specifications), T_a = -40 to +85°C (wide-range specifications)

Item	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Rewrite/erase cycle*1	N_{PEC}	1000	—	—	Times	
Data hold time	T_{DRP}	30*2	—	—	Year	Ta = +85°C

Notes: 1. Definition of rewrite/erase cycle:
The rewrite/erase cycle is the number of erasing for each block. When the rewrite/erase cycle is n times (n = 1000), erasing can be performed n times for each block. For instance, when 256-byte writing is performed 32 times for different addresses in 8-Kbyte block and then the entire block is erased, the rewrite/erase cycle is counted as one. However, writing to the same address for several times as one erasing is not enabled (overwriting is prohibited).
2. This value is based on the result of the reliability test.

ROM (Flash Memory for Code Storage) Characteristics (2)

Conditions: V_{CC} = $PLLV_{CC}$ = AV_{CC} = 3.0 to 3.6 V, V_{REFH} = 3.0 V to AV_{CC}, V_{SS} = $PLLV_{SS}$ = V_{REFL} = 0 V
Operating temperature range during programming/erasing:
T_a = -20 to +85°C (regular specifications), T_a = -40 to +85°C (wide-range specifications)

Item		Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Programming time	256 bytes	t_{P256}	—	2	12	ms	PCLK = 50 MHz
	8 Kbytes	t_{P8K}	—	45	100	ms	N_{PEC} ≤ 100
	256 bytes	t_{P256}	—	2.4	14.4	ms	PCLK = 50 MHz
	8 Kbytes	t_{P8K}	—	54	120	ms	N_{PEC} > 100
Erasure time	8 Kbytes	t_{E8K}	—	50	120	ms	PCLK = 50 MHz
	64 Kbytes	t_{E64K}	—	400	875	ms	N_{PEC} ≤ 100
	128 Kbytes	t_{E128K}	—	800	1750	ms	
	8 Kbytes	t_{E8K}	—	60	144	ms	PCLK = 50 MHz
	64 Kbytes	t_{E64K}	—	480	1050	ms	N_{PEC} > 100
	128 Kbytes	t_{E128K}	—	960	2100	ms	
Suspend delay time during writing		t_{SPD}	—	—	120	µs	Figure 29.29
First suspend delay time during erasing (in suspend priority mode)		t_{SESD1}	—	—	120	µs	PCLK = 50 MHz
Second suspend delay time during erasing (in suspend priority mode)		t_{SESD2}	—	—	1.7	ms	
Suspend delay time during erasing (in erasure priority mode)		t_{SEED}	—	—	1.7	ms	

- RX610 Group Data Flash (Flash Memory for Data Storage) Characteristics

  Refer to Table 29.12 in RX610 Group User's Manual: Hardware Rev.1.20

Before change

Data Flash (Flash Memory for Data Storage) Characteristics

Conditions: V_{CC} = $PLLV_{CC}$ = AV_{CC} = 3.0 to 3.6 V, V_{REFH} = 3.0 V to AV_{CC}, V_{SS} = $PLLV_{SS}$ = V_{REFL} = 0 V
Operating temperature range during programming/erasing:
T_a = -20 to +85°C (regular specifications), T_a = -40 to +85°C (wide-range specifications)

Item		Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Programming time	8 bytes	t_{DP8}	—	0.4	2	ms	PCLK = 50-MHz operation
	128 bytes	t_{DP128}	—	1	5	ms	
Erasure time	8 Kbytes	t_{DE8K}	—	300	900	ms	PCLK = 50-MHz operation
Blank check time	8 bytes	t_{DBC8}	—	—	30	µs	PCLK = 50-MHz operation
	8 Kbytes	t_{DBC8K}	—	—	2.5	ms	
Rewrite/erase cycle*1		N_{DPEC}	30000*2	—	—	Times	
Suspend delay time during writing		t_{DSPD}	—	—	120	µs	Figure 29.29 PCLK = 50-MHz operation
First suspend delay time during erasing (in suspend priority mode)		t_{DSESD1}	—	—	120	µs	
Second suspend delay time during erasing (in suspend priority mode)		t_{DSESD2}	—	—	1.7	ms	
Suspend delay time during erasing (in erasure priority mode)		t_{DSEED}	—	—	1.7	ms	
Data hold time*3		T_{DDRP}	10	—	—	Year	

Notes: 1. Definition of rewrite/erase cycle:
The rewrite/erase cycle is the number of erasing for each block. When the rewrite/erase cycle is n times (n = 30000), erasing can be performed n times for each block. For instance, when 128-byte writing is performed 64 times for different addresses in 8-Kbyte block and then the entire block is erased, the rewrite/erase cycle is counted as one. However, writing to the same address for several times as one erasing is not enabled (over writing is prohibited).
2. This indicates the minimum number that guarantees the characteristics after rewriting. (The guaranteed value is in the range from one to the minimum number.)
3. This indicates the characteristic when rewrite is performed within the specification range including the minimum number.

After change

Data Flash (Flash Memory for Data Storage) Characteristics (1)

Conditions: V_{CC} = $PLLV_{CC}$ = AV_{CC} = 3.0 to 3.6 V, V_{REFH} = 3.0 V to AV_{CC}, V_{SS} = $PLLV_{SS}$ = V_{REFL} = 0 V
Operating temperature range during programming/erasing:
T_a = -20 to +85°C (regular specifications), T_a = -40 to +85°C (wide-range specifications)

Item	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Rewrite/erase cycle*1	N_{DPEC}	30000	—	—	Times	
Data hold time	T_{DDRP}	30*2	—	—	Year	T_a = +85°C

Notes: 1. Definition of rewrite/erase cycle:
The rewrite/erase cycle is the number of erasing for each block. When the rewrite/erase cycle is n times (n = 30000), erasing can be performed n times for each block. For instance, when 128-byte writing is performed 64 times for different addresses in 8-Kbyte block and then the entire block is erased, the rewrite/erase cycle is counted as one. However, writing to the same address for several times as one erasing is not enabled (overwriting is prohibited).
2. This value is based on the result of the reliability test.

Data Flash (Flash Memory for Data Storage) Characteristics (2)

Conditions: V_{CC} = $PLLV_{CC}$ = AV_{CC} = 3.0 to 3.6 V, V_{REFH} = 3.0 V to AV_{CC}, V_{SS} = $PLLV_{SS}$ = V_{REFL} = 0 V
Operating temperature range during programming/erasing:
T_a = -20 to +85°C (regular specifications), T_a = -40 to +85°C (wide-range specifications)

Item		Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Programming time	8 bytes	t_{DP8}	—	0.4	2	ms	PCLK = 50-MHz operation
	128 bytes	t_{DP128}	—	1	5	ms	
Erasure time	8 Kbytes	t_{DE8K}	—	300	900	ms	PCLK = 50-MHz operation
Blank check time	8 bytes	t_{DBC8}	—	—	30	µs	PCLK = 50-MHz operation
	8 Kbytes	t_{DBC8K}	—	—	2.5	ms	
Suspend delay time during writing		t_{DSPD}	—	—	120	µs	Figure 29.29 PCLK = 50-MHz operation
First suspend delay time during erasing (in suspend priority mode)		t_{DSESD1}	—	—	120	µs	
Second suspend delay time during erasing (in suspend priority mode)		t_{DSESD2}	—	—	1.7	ms	
Suspend delay time during erasing (in erasure priority mode)		t_{DSEED}	—	—	1.7	ms	

- RX62G Group ROM (Flash Memory for Code Storage) Characteristics

  Refer to Table 33.20 in RX62G Group User's Manual: Hardware Rev.1.00

Before change

ROM (Flash Memory for Code Storage) Characteristics

VCC = PLLVCC = 4.0 to 5.5 V, VSS = PLLVSS = AVSS0 = AVSS = VREFL0 = 0 V
AVCC0 = AVCC = 4.0 to 5.5 V, VREFH0 = 4.0 V to AVCC0, VREF = 4.0 V to AVCC
Temperature range for the programming/erasure operation: Ta = -40 to +85°C.

Item		Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Programming time	256 bytes	t_{P256}	—	2	12	ms	PCLK = 50 MHz $N_{PEC} \leq 100$
	4 Kbytes	t_{P4K}	—	23	50	ms	
	16 Kbytes	t_{P16K}	—	90	200	ms	
	256 bytes	t_{P256}	—	2.4	14.4	ms	PCLK = 50 MHz $N_{PEC} > 100$
	4 Kbytes	t_{P4K}	—	27.6	60	ms	
	16 Kbytes	t_{P16K}	—	108	240	ms	
Erasure time	4 Kbytes	t_{E4K}	—	25	60	ms	PCLK = 50 MHz $N_{PEC} \leq 100$
	16 Kbytes	t_{E16K}	—	100	240	ms	
	4 Kbytes	t_{E4K}	—	30	72	ms	PCLK = 50 MHz $N_{PEC} > 100$
	16 Kbytes	t_{E16K}	—	120	288	ms	
Rewrite/erase cycle*1		N_{PEC}	1000*2	—	—	Times	
Suspend delay time during writing		t_{SPD}	—	—	120	µs	Figure 33.24 PCLK = 50 MHz
First suspend delay time during erasing (in suspend priority mode)		t_{SESD1}	—	—	120	µs	
Second suspend delay time during erasing (in suspend priority mode)		t_{SESD2}	—	—	1.7	ms	
Suspend delay time during erasing (in erasure priority mode)		t_{SEED}	—	—	1.7	ms	
Data hold time*3		T_{DRP}	10	—	—	Year	

Note 1. Definition of rewrite/erase cycle:
The rewrite/erase cycle is the number of erasing for each block. When the rewrite/erase cycle is n times (n = 1000), erasing can be performed n times for each block. For instance, when 256-byte writing is performed 16 times for different addresses in 4-Kbyte block and then the entire block is erased, the rewrite/erase cycle is counted as one. However, writing to the same address for several times as one erasing is not enabled (overwriting is prohibited).

Note 2. This indicates the minimum number that guarantees the characteristics after rewriting. (The guaranteed value is in the range from one to the minimum number.)

Note 3. This indicates the characteristic when rewrite is performed within the specification range including the minimum number.

After change

ROM (Flash Memory for Code Storage) Characteristics (1)

VCC = PLLVCC = 4.0 to 5.5 V, VSS = PLLVSS = AVSS0 = AVSS = VREFL0 = 0 V
AVCC0 = AVCC = 4.0 to 5.5 V, VREFH0 = 4.0 V to AVCC0, VREF = 4.0 V to AVCC
Temperature range for the programming/erasure operation: Ta = -40 to +85°C

Item	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Rewrite/erase cycle*1	N_{PEC}	1000	—	—	Times	
Data hold time	T_{DRP}	30*2	—	—	Year	Ta = +85°C

Note 1. Definition of rewrite/erase cycle:
The rewrite/erase cycle is the number of erasing for each block. When the rewrite/erase cycle is n times (n = 1000), erasing can be performed n times for each block. For instance, when 256-byte writing is performed 16 times for different addresses in 4-Kbyte block and then the entire block is erased, the rewrite/erase cycle is counted as one. However, writing to the same address for several times as one erasing is not enabled (overwriting is prohibited).
Note 2. This value is based on the result of the reliability test.

ROM (Flash Memory for Code Storage) Characteristics (2)

VCC = PLLVCC = 4.0 to 5.5 V, VSS = PLLVSS = AVSS0 = AVSS = VREFL0 = 0 V
AVCC0 = AVCC = 4.0 to 5.5 V, VREFH0 = 4.0 V to AVCC0, VREF = 4.0 V to AVCC
Temperature range for the programming/erasure operation: Ta = -40 to +85°C

Item		Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Programming time	256 bytes	t_{P256}	—	2	12	ms	PCLK = 50 MHz, N_{PEC} ≤ 100
	4 Kbytes	t_{P4K}	—	23	50	ms	
	16 Kbytes	t_{P16K}	—	90	200	ms	PCLK = 50 MHz, N_{PEC} > 100
	256 bytes	t_{P256}	—	2.4	14.4	ms	
	4 Kbytes	t_{P4K}	—	27.6	60	ms	PCLK = 50 MHz, N_{PEC} ≤ 100
	16 Kbytes	t_{P16K}	—	108	240	ms	
Erasure time	4 Kbytes	t_{E4K}	—	25	60	ms	
	16 Kbytes	t_{E16K}	—	100	240	ms	PCLK = 50 MHz, N_{PEC} > 100
	4 Kbytes	t_{E4K}	—	30	72	ms	
	16 Kbytes	t_{E16K}	—	120	288	ms	
Suspend delay time during writing		t_{SPD}	—	—	120	µs	Figure 33.24 PCLK = 50 MHz
First suspend delay time during erasing (in suspend priority mode)		t_{SESD1}	—	—	120	µs	
Second suspend delay time during erasing (in suspend priority mode)		t_{SESD2}	—	—	1.7	ms	
Suspend delay time during erasing (in erasure priority mode)		t_{SEED}	—	—	1.7	ms	

- RX62G Group Data Flash (Flash Memory for Data Storage) Characteristics

  Refer to Table 33.21 in RX62G Group User's Manual: Hardware Rev.1.00

Before change

Data Flash (Flash Memory for Data Storage) Characteristics

VCC = PLLVCC = 4.0 to 5.5 V, VSS = PLLVSS = AVSS0 = AVSS = VREFL0 = 0 V
AVCC0 = AVCC = 4.0 to 5.5 V, VREFH0 = 4.0 V to AVCC0, VREF = 4.0 V to AVCC
Temperature range for the programming/erasure operation: Ta = -40 to +85°C.

Item		Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Programming time	8 bytes	t_{DP8}	—	0.4	2	ms	PCLK = 50 MHz
	128 bytes	t_{DP128}	—	1	5	ms	
Erasure time	2 Kbytes	t_{DE2K}	—	70	250	ms	PCLK = 50 MHz
Blank check time	8 bytes	t_{DBC8}	—	—	30	µs	PCLK = 50 MHz
	2 Kbytes	t_{DBC2K}	—	—	0.7	ms	
Rewrite/erase cycle*1		N_{DPEC}	30000*2	—	—	Times	
Suspend delay time during writing		t_{DSPD}	—	—	120	µs	Figure 33.24 PCLK = 50 MHz
First suspend delay time during erasing (in suspend priority mode)		t_{DSESD1}	—	—	120	µs	
Second suspend delay time during erasing (in suspend priority mode)		t_{DSESD2}	—	—	1.7	ms	
Suspend delay time during erasing (in erasure priority mode)		t_{DSEED}	—	—	1.7	ms	
Data hold time*3		T_{DDRP}	10	—	—	Year	

Note 1. Definition of rewrite/erase cycle:
The rewrite/erase cycle is the number of erasing for each block. When the rewrite/erase cycle is n times (n = 30000), erasing can be performed n times for each block. For instance, when 128-byte writing is performed 16 times for different addresses in 2-Kbyte block and then the entire block is erased, the rewrite/erase cycle is counted as one. However, writing to the same address for several times as one erasing is not enabled (overwriting is prohibited).

Note 2. This indicates the minimum number that guarantees the characteristics after rewriting. (The guaranteed value is in the range from one to the minimum number.)

Note 3. This indicates the characteristic when rewrite is performed within the specification range including the minimum number.

After change

Data Flash (Flash Memory for Data Storage) Characteristics (1)

VCC = PLLVCC = 4.0 to 5.5 V, VSS = PLLVSS = AVSS0 = AVSS = VREFL0 = 0 V
AVCC0 = AVCC = 4.0 to 5.5 V, VREFH0 = 4.0 V to AVCC0, VREF = 4.0 V to AVCC
Temperature range for the programming/erasure operation: Ta = -40 to +85°C.

Item	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Rewrite/erase cycle*1	N_{DPEC}	30000	—	—	Times	
Data hold time	T_{DDRP}	30*2	—	—	Year	T_a = +85°C

Note 1. Definition of rewrite/erase cycle:
The rewrite/erase cycle is the number of erasing for each block. When the rewrite/erase cycle is n times (n = 30000), erasing can be performed n times for each block. For instance, when 128-byte writing is performed 16 times for different addresses in 2-Kbyte block and then the entire block is erased, the rewrite/erase cycle is counted as one. However, writing to the same address for several times as one erasing is not enabled (overwriting is prohibited).
Note 2. This value is based on the result of the reliability test.

Data Flash (Flash Memory for Data Storage) Characteristics (2)

VCC = PLLVCC = 4.0 to 5.5 V, VSS = PLLVSS = AVSS0 = AVSS = VREFL0 = 0 V
AVCC0 = AVCC = 4.0 to 5.5 V, VREFH0 = 4.0 V to AVCC0, VREF = 4.0 V to AVCC
Temperature range for the programming/erasure operation: Ta = -40 to +85°C.

Item		Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Programming time	8 bytes	t_{DP8}	—	0.4	2	ms	PCLK = 50 MHz
	128 bytes	t_{DP128}	—	1	5	ms	
Erasure time	2 Kbytes	t_{DE2K}	—	70	250	ms	PCLK = 50 MHz
Blank check time	8 bytes	t_{DBC8}	—	—	30	µs	PCLK = 50 MHz
	2 Kbytes	t_{DBC2K}	—	—	0.7	ms	
Suspend delay time during writing		t_{DSPD}	—	—	120	µs	Figure 33.24 PCLK = 50 MHz
First suspend delay time during erasing (in suspend priority mode)		t_{DSESD1}	—	—	120	µs	
Second suspend delay time during erasing (in suspend priority mode)		t_{DSESD2}	—	—	1.7	ms	
Suspend delay time during erasing (in erasure priority mode)		t_{DSEED}	—	—	1.7	ms	

- RX62N Group, RX621 Group ROM (Flash Memory for Code Storage) Characteristics

  Refer to Table 41.25 in RX62N Group, RX621 Group User's Manual: Hardware Rev.1.30

Before change

ROM (Flash Memory for Code Storage) Characteristics

Conditions: VCC = PLLVCC = AVCC = VCC_USB = 2.7 to 3.6V, VREFH = 2.7V to AVCC
VSS = PLLVSS = AVSS = VREFL = VSS_USB = 0V
Temperature range for the programming/erasure operation: T_a = -40 to +85°C

Item		Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Programming time	256 bytes	t_{P256}	—	2	12	ms	PCLK = 50 MHz N_{PEC} ≤ 100
	4 Kbytes	t_{P4K}	—	23	50	ms	
	16 Kbytes	t_{P16K}	—	90	200	ms	
	256 bytes	t_{P256}	—	2.4	14.4	ms	PCLK = 50 MHz N_{PEC} > 100
	4 Kbytes	t_{P4K}	—	27.6	60	ms	
	16 Kbytes	t_{P16K}	—	108	240	ms	
Erasure time	4 Kbytes	t_{E4K}	—	25	60	ms	PCLK = 50 MHz N_{PEC} ≤ 100
	16 Kbytes	t_{E16K}	—	100	240	ms	
	4 Kbytes	t_{E4K}	—	30	72	ms	PCLK = 50 MHz N_{PEC} > 100
	16 Kbytes	t_{E16K}	—	120	288	ms	
Rewrite/erase cycle*1		N_{PEC}	1000*2	—	—	Times	
Suspend delay time during writing		t_{SPD}	—	—	120	µs	Figure 41.67 PCLK = 50-MHz operation
First suspend delay time during erasing (in suspend priority mode)		t_{SESD1}	—	—	120	µs	
Second suspend delay time during erasing (in suspend priority mode)		t_{SESD2}	—	—	1.7	ms	
Suspend delay time during erasing (in erasure priority mode)		t_{SEED}	—	—	1.7	ms	
Data hold time*3		T_{DRP}	10	—	—	Year	

Note 1. Definition of rewrite/erase cycle:
The rewrite/erase cycle is the number of erasing for each block. When the rewrite/erase cycle is n times (n = 1000), erasing can be performed n times for each block. For instance, when 256-byte writing is performed 16 times for different addresses in 4-Kbyte block and then the entire block is erased, the rewrite/erase cycle is counted as one. However, writing to the same address for several times as one erasing is not enabled (over writing is prohibited).

Note 2. This indicates the minimum number that guarantees the characteristics after rewriting. (The guaranteed value is in the range from one to the minimum number.)

Note 3. This indicates the characteristic when rewrite is performed within the specification range including the minimum number.

After change

ROM (Flash Memory for Code Storage) Characteristics (1)

Conditions: VCC = PLLVCC = AVCC = VCC_USB = 2.7 to 3.6V, VREFH = 2.7V to AVCC
VSS = PLLVSS = AVSS = VREFL = VSS_USB = 0V
Temperature range for the programming/erasure operation: T_a = -40 to +85°C

Item	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Rewrite/erase cycle*1	N_{PEC}	1000	—	—	Times	
Data hold time	T_{DRP}	30*2	—	—	Year	Ta = +85°C

Note 1. Definition of rewrite/erase cycle:
The rewrite/erase cycle is the number of erasing for each block. When the rewrite/erase cycle is n times (n = 1000), erasing can be performed n times for each block. For instance, when 256-byte writing is performed 16 times for different addresses in 4-Kbyte block and then the entire block is erased, the rewrite/erase cycle is counted as one. However, writing to the same address for several times as one erasing is not enabled (overwriting is prohibited).
Note 2. This value is based on the result of the reliability test.

• ROM (Flash Memory for Code Storage) Characteristics (2)

Conditions: VCC = PLLVCC = AVCC = VCC_USB = 2.7 to 3.6V, VREFH = 2.7V to AVCC
VSS = PLLVSS = AVSS = VREFL = VSS_USB = 0V
Temperature range for the programming/erasure operation: T_a = -40 to +85°C

Item		Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Programming time	256 bytes	t_{P256}	—	2	12	ms	PCLK = 50 MHz $N_{PEC} \leq 100$
	4 Kbytes	t_{P4K}	—	23	50	ms	
	16 Kbytes	t_{P16K}	—	90	200	ms	
	256 bytes	t_{P256}	—	2.4	14.4	ms	PCLK = 50 MHz $N_{PEC} > 100$
	4 Kbytes	t_{P4K}	—	27.6	60	ms	
	16 Kbytes	t_{P16K}	—	108	240	ms	
Erasure time	4 Kbytes	t_{E4K}	—	25	60	ms	PCLK = 50 MHz $N_{PEC} \leq 100$
	16 Kbytes	t_{E16K}	—	100	240	ms	
	4 Kbytes	t_{E4K}	—	30	72	ms	PCLK = 50 MHz $N_{PEC} > 100$
	16 Kbytes	t_{E16K}	—	120	288	ms	
Suspend delay time during writing		t_{SPD}	—	—	120	µs	Figure 41.67 PCLK = 50 MHz
First suspend delay time during erasing (in suspend priority mode)		t_{SESD1}	—	—	120	µs	
Second suspend delay time during erasing (in suspend priority mode)		t_{SESD2}	—	—	1.7	ms	
Suspend delay time during erasing (in erasure priority mode)		t_{SEED}	—	—	1.7	ms	

- RX62N Group, RX621 Group Data Flash (Flash Memory for Data Storage) Characteristics
  Refer to Table 41.26 in RX62N Group, RX621 Group User's Manual: Hardware Rev.1.30

Before change

Data Flash (Flash Memory for Data Storage) Characteristics

Conditions: VCC = PLLVCC = AVCC = VCC_USB = 2.7 to 3.6V, VREFH = 2.7V to AVCC
VSS = PLLVSS = AVSS = VREFL = VSS_USB = 0V
Temperature range for the programming/erasure operation: Ta = -40 to +85°C

Item		Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Programming time	8 bytes	t_{DP8}	—	0.4	2	ms	PCLK = 50-MHz operation
	128 bytes	t_{DP128}	—	1	5	ms	
Erasure time	2 Kbytes	t_{DE2K}	—	70	250	ms	PCLK = 50-MHz operation
Blank check time	8 bytes	t_{DBC8}	—	—	30	µs	PCLK = 50-MHz operation
	2 Kbytes	t_{DBC2K}	—	—	0.7	ms	
Rewrite/erase cycle*1		N_{DPEC}	30000*2	—	—	Times	
Suspend delay time during writing		t_{DSPD}	—	—	120	µs	Figure 41.67 PCLK = 50-MHz operation
First suspend delay time during erasing (in suspend priority mode)		t_{DSESD1}	—	—	120	µs	
Second suspend delay time during erasing (in suspend priority mode)		t_{DSESD2}	—	—	1.7	ms	
Suspend delay time during erasing (in erasure priority mode)		t_{DSEED}	—	—	1.7	ms	
Data hold time*3		T_{DDRP}	10	—	—	Year	

Note 1. Definition of rewrite/erase cycle:
The rewrite/erase cycle is the number of erasing for each block. When the rewrite/erase cycle is n times (n = 30000), erasing can be performed n times for each block. For instance, when 128-byte writing is performed 16 times for different addresses in 2-Kbyte block and then the entire block is erased, the rewrite/erase cycle is counted as one. However, writing to the same address for several times as one erasing is not enabled (over writing is prohibited).
Note 2. This indicates the minimum number that guarantees the characteristics after rewriting. (The guaranteed value is in the range from one to the minimum number.)
Note 3. This indicates the characteristic when rewrite is performed within the specification range including the minimum number.

After change

Data Flash (Flash Memory for Data Storage) Characteristics (1)

Conditions: VCC = PLLVCC = AVCC = VCC_USB = 2.7 to 3.6V, VREFH = 2.7V to AVCC
VSS = PLLVSS = AVSS = VREFL = VSS_USB = 0V
Temperature range for the programming/erasure operation: Ta = -40 to +85°C

Item	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Rewrite/erase cycle*1	N_{DPEC}	30000	—	—	Times	
Data hold time	T_{DDRP}	30*2	—	—	Year	T_a = +85°C

Note 1. Definition of rewrite/erase cycle:
The rewrite/erase cycle is the number of erasing for each block. When the rewrite/erase cycle is n times (n = 30000), erasing can be performed n times for each block. For instance, when 128-byte writing is performed 16 times for different addresses in 2-Kbyte block and then the entire block is erased, the rewrite/erase cycle is counted as one. However, writing to the same address for several times as one erasing is not enabled (overwriting is prohibited).
Note 2. This value is based on the result of the reliability test.

Data Flash (Flash Memory for Data Storage) Characteristics (2)

Conditions: VCC = PLLVCC = AVCC = VCC_USB = 2.7 to 3.6V, VREFH = 2.7V to AVCC
VSS = PLLVSS = AVSS = VREFL = VSS_USB = 0V
Temperature range for the programming/erasure operation: Ta = -40 to +85°C

Item		Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Programming time	8 bytes	t_{DP8}	—	0.4	2	ms	PCLK = 50 MHz
	128 bytes	t_{DP128}	—	1	5	ms	
Erasure time	2 Kbytes	t_{DE2K}	—	70	250	ms	PCLK = 50 MHz
Blank check time	8 bytes	t_{DBC8}	—	—	30	µs	PCLK = 50 MHz
	2 Kbytes	t_{DBC2K}	—	—	0.7	ms	
Suspend delay time during writing		t_{DSPD}	—	—	120	µs	Figure 41.67 PCLK = 50 MHz
First suspend delay time during erasing (in suspend priority mode)		t_{DSESD1}	—	—	120	µs	
Second suspend delay time during erasing (in suspend priority mode)		t_{DSESD2}	—	—	1.7	ms	
Suspend delay time during erasing (in erasure priority mode)		t_{DSEED}	—	—	1.7	ms	

- RX62T Group ROM (Flash Memory for Code Storage) Characteristics

  Refer to Table 33.19 in RX62T Group User's Manual: Hardware Rev.1.30

Before change

ROM (Flash Memory for Code Storage) Characteristics

Note:Items for which test conditions are not specifically stated in the table below have the same values under conditions 1 to 3.
Condition 1: VCC = PLLVCC = 2.7 to 3.6 V, VSS = PLLVSS = AVSS0 = AVSS = VREFL0 = 0 V
AVCC0 = AVCC = 3.0 to 3.6 V, VREFH0 = 3.0 V to AVCC0, VREF = 3.0 V to AVCC
Condition 2: VCC = PLLVCC = 2.7 to 3.6 V, VSS = PLLVSS = AVSS0 = AVSS = VREFL0 = 0 V
AVCC0 = AVCC = 4.0 to 5.5 V, VREFH0 = 4.0 V to AVCC0, VREF = 4.0 V to AVCC
Condition 3: VCC = PLLVCC = 4.0 to 5.5 V, VSS = PLLVSS = AVSS0 = AVSS = VREFL0 = 0 V
AVCC0 = AVCC = 4.0 to 5.5 V, VREFH0 = 4.0 V to AVCC0, VREF = 4.0 V to AVCC
Temperature range for the programming/erasure operation:
Ta = -40 to +85°C. Ta is the same under conditions 1 to 3.

Item		Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Programming time	256 bytes	t_{P256}	—	2	12	ms	PCLK = 50 MHz $N_{PEC} \leq 100$
	4 Kbytes	t_{P4K}	—	23	50	ms	
	16 Kbytes	t_{P16K}	—	90	200	ms	
	256 bytes	t_{P256}	—	2.4	14.4	ms	PCLK = 50 MHz $N_{PEC} > 100$
	4 Kbytes	t_{P4K}	—	27.6	60	ms	
	16 Kbytes	t_{P16K}	—	108	240	ms	
Erasure time	4 Kbytes	t_{E4K}	—	25	60	ms	PCLK = 50 MHz $N_{PEC} \leq 100$
	16 Kbytes	t_{E16K}	—	100	240	ms	
	4 Kbytes	t_{E4K}	—	30	72	ms	PCLK = 50 MHz $N_{PEC} > 100$
	16 Kbytes	t_{E16K}	—	120	288	ms	
Rewrite/erase cycle*1		N_{PEC}	1000*2	—	—	Times	
Suspend delay time during writing		t_{SPD}	—	—	120	µs	Figure 33.24 PCLK = 50 MHz
First suspend delay time during erasing (in suspend priority mode)		t_{SESD1}	—	—	120	µs	
Second suspend delay time during erasing (in suspend priority mode)		t_{SESD2}	—	—	1.7	ms	
Suspend delay time during erasing (in erasure priority mode)		t_{SEED}	—	—	1.7	ms	
Data hold time*3		T_{DRP}	10	—	—	Year	

Note 1. Definition of rewrite/erase cycle:
The rewrite/erase cycle is the number of erasing for each block. When the rewrite/erase cycle is n times (n = 1000), erasing can be performed n times for each block. For instance, when 256-byte writing is performed 16 times for different addresses in 4-Kbyte block and then the entire block is erased, the rewrite/erase cycle is counted as one. However, writing to the same address for several times as one erasing is not enabled (overwriting is prohibited).
Note 2. This indicates the minimum number that guarantees the characteristics after rewriting. (The guaranteed value is in the range from one to the minimum number.)
Note 3. This indicates the characteristic when rewrite is performed within the specification range including the minimum number.

After change

ROM (Flash Memory for Code Storage) Characteristics (1)

Note: Items for which test conditions are not specifically stated in the table below have the same values under conditions 1 to 3.
Condition 1: VCC = PLLVCC = 2.7 to 3.6 V, VSS = PLLVSS = AVSS0 = AVSS = VREFL0 = 0 V
AVCC0 = AVCC = 3.0 to 3.6 V, VREFH0 = 3.0 V to AVCC0, VREF = 3.0 V to AVCC
Condition 2: VCC = PLLVCC = 2.7 to 3.6 V, VSS = PLLVSS = AVSS0 = AVSS = VREFL0 = 0 V
AVCC0 = AVCC = 4.0 to 5.5 V, VREFH0 = 4.0 V to AVCC0, VREF = 4.0 V to AVCC
Condition 3: VCC = PLLVCC = 4.0 to 5.5 V, VSS = PLLVSS = AVSS0 = AVSS = VREFL0 = 0 V
AVCC0 = AVCC = 4.0 to 5.5 V, VREFH0 = 4.0 V to AVCC0, VREF = 4.0 V to AVCC
Temperature range for the programming/erasure operation:
Ta = -40 to +85°C. Ta is the same under conditions 1 to 3.

Item	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Rewrite/erase cycle*1	N_{PEC}	1000	—	—	Times	
Data hold time	T_{DRP}	30*2	—	—	Year	Ta = +85°C

Note 1. Definition of rewrite/erase cycle:
The rewrite/erase cycle is the number of erasing for each block. When the rewrite/erase cycle is n times (n = 1000), erasing can be performed n times for each block. For instance, when 256-byte writing is performed 16 times for different addresses in 4-Kbyte block and then the entire block is erased, the rewrite/erase cycle is counted as one. However, writing to the same address for several times as one erasing is not enabled (overwriting is prohibited).
Note 2. This value is based on the result of the reliability test.

ROM (Flash Memory for Code Storage) Characteristics (2)

Note: Items for which test conditions are not specifically stated in the table below have the same values under conditions 1 to 3.
Condition 1: VCC = PLLVCC = 2.7 to 3.6 V, VSS = PLLVSS = AVSS0 = AVSS = VREFL0 = 0 V
AVCC0 = AVCC = 3.0 to 3.6 V, VREFH0 = 3.0 V to AVCC0, VREF = 3.0 V to AVCC
Condition 2: VCC = PLLVCC = 2.7 to 3.6 V, VSS = PLLVSS = AVSS0 = AVSS = VREFL0 = 0 V
AVCC0 = AVCC = 4.0 to 5.5 V, VREFH0 = 4.0 V to AVCC0, VREF = 4.0 V to AVCC
Condition 3: VCC = PLLVCC = 4.0 to 5.5 V, VSS = PLLVSS = AVSS0 = AVSS = VREFL0 = 0 V
AVCC0 = AVCC = 4.0 to 5.5 V, VREFH0 = 4.0 V to AVCC0, VREF = 4.0 V to AVCC
Temperature range for the programming/erasure operation:
Ta = -40 to +85°C. Ta is the same under conditions 1 to 3.

Item		Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Programming time	256 bytes	t_{P256}	—	2	12	ms	PCLK = 50 MHz $N_{PEC} \leq 100$
	4 Kbytes	t_{P4K}	—	23	50	ms	
	16 Kbytes	t_{P16K}	—	90	200	ms	
	256 bytes	t_{P256}	—	2.4	14.4	ms	PCLK = 50 MHz $N_{PEC} > 100$
	4 Kbytes	t_{P4K}	—	27.6	60	ms	
	16 Kbytes	t_{P16K}	—	108	240	ms	
Erasure time	4 Kbytes	t_{E4K}	—	25	60	ms	PCLK = 50 MHz $N_{PEC} \leq 100$
	16 Kbytes	t_{E16K}	—	100	240	ms	
	4 Kbytes	t_{E4K}	—	30	72	ms	PCLK = 50 MHz $N_{PEC} > 100$
	16 Kbytes	t_{E16K}	—	120	288	ms	
Suspend delay time during writing		t_{SPD}	—	—	120	µs	Figure 33.24 PCLK = 50 MHz
First suspend delay time during erasing (in suspend priority mode)		t_{SESD1}	—	—	120	µs	
Second suspend delay time during erasing (in suspend priority mode)		t_{SESD2}	—	—	1.7	ms	
Suspend delay time during erasing (in erasure priority mode)		t_{SEED}	—	—	1.7	ms	

- RX62T Group Data Flash (Flash Memory for Data Storage) Characteristics

  Refer to Table 33.20 in RX62T Group User's Manual: Hardware Rev.1.30

Before change

Data Flash (Flash Memory for Data Storage) Characteristics

Note:Items for which test conditions are not specifically stated in the table below have the same values under conditions 1 to 3.
Condition 1: VCC = PLLVCC = 2.7 to 3.6 V, VSS = PLLVSS = AVSS0 = AVSS = VREFL0 = 0 V
AVCC0 = AVCC = 3.0 to 3.6 V, VREFH0 = 3.0 V to AVCC0, VREF = 3.0 V to AVCC
Condition 2: VCC = PLLVCC = 2.7 to 3.6 V, VSS = PLLVSS = AVSS0 = AVSS = VREFL0 = 0 V
AVCC0 = AVCC = 4.0 to 5.5 V, VREFH0 = 4.0 V to AVCC0, VREF = 4.0 V to AVCC
Condition 3: VCC = PLLVCC = 4.0 to 5.5 V, VSS = PLLVSS = AVSS0 = AVSS = VREFL0 = 0 V
AVCC0 = AVCC = 4.0 to 5.5 V, VREFH0 = 4.0 V to AVCC0, VREF = 4.0 V to AVCC
Temperature range for the programming/erasure operation:
Ta = -40 to +85°C. Ta is the same under conditions 1 to 3.

Item		Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Programming time	8 bytes	t_{DP8}	—	0.4	2	ms	PCLK = 50 MHz
	128 bytes	t_{DP128}	—	1	5	ms	
Erasure time	2 Kbytes	t_{DE2K}	—	70	250	ms	PCLK = 50 MHz
Blank check time	8 bytes	t_{DBC8}	—	—	30	µs	PCLK = 50 MHz
	2 Kbytes	t_{DBC2K}	—	—	0.7	ms	
Rewrite/erase cycle*1		N_{DPEC}	30000*2	—	—	Times	
Suspend delay time during writing		t_{DSPD}	—	—	120	µs	Figure 33.24 PCLK = 50 MHz
First suspend delay time during erasing (in suspend priority mode)		t_{DSESD1}	—	—	120	µs	
Second suspend delay time during erasing (in suspend priority mode)		t_{DSESD2}	—	—	1.7	ms	
Suspend delay time during erasing (in erasure priority mode)		t_{DSEED}	—	—	1.7	ms	
Data hold time*3		T_{DDRP}	10	—	—	Year	

Note 1. Definition of rewrite/erase cycle:
The rewrite/erase cycle is the number of erasing for each block. When the rewrite/erase cycle is n times (n = 30000), erasing can be performed n times for each block. For instance, when 128-byte writing is performed 16 times for different addresses in 2-Kbyte block and then the entire block is erased, the rewrite/erase cycle is counted as one. However, writing to the same address for several times as one erasing is not enabled (overwriting is prohibited).
Note 2. This indicates the minimum number that guarantees the characteristics after rewriting. (The guaranteed value is in the range from one to the minimum number.)
Note 3. This indicates the characteristic when rewrite is performed within the specification range including the minimum number.

After change

Data Flash (Flash Memory for Data Storage) Characteristics (1)

Note: Items for which test conditions are not specifically stated in the table below have the same values under conditions 1 to 3.
Condition 1: VCC = PLLVCC = 2.7 to 3.6 V, VSS = PLLVSS = AVSS0 = AVSS = VREFL0 = 0 V
AVCC0 = AVCC = 3.0 to 3.6 V, VREFH0 = 3.0 V to AVCC0, VREF = 3.0 V to AVCC
Condition 2: VCC = PLLVCC = 2.7 to 3.6 V, VSS = PLLVSS = AVSS0 = AVSS = VREFL0 = 0 V
AVCC0 = AVCC = 4.0 to 5.5 V, VREFH0 = 4.0 V to AVCC0, VREF = 4.0 V to AVCC
Condition 3: VCC = PLLVCC = 4.0 to 5.5 V, VSS = PLLVSS = AVSS0 = AVSS = VREFL0 = 0 V
AVCC0 = AVCC = 4.0 to 5.5 V, VREFH0 = 4.0 V to AVCC0, VREF = 4.0 V to AVCC
Temperature range for the programming/erasure operation:
Ta = -40 to +85°C. Ta is the same under conditions 1 to 3.

Item	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Rewrite/erase cycle*[1]	N_{DPEC}	30000	—	—	Times	
Data hold time	T_{DDRP}	30*[2]	—	—	Year	T_a = +85°C

Note 1. Definition of rewrite/erase cycle:
The rewrite/erase cycle is the number of erasing for each block. When the rewrite/erase cycle is n times (n = 30000), erasing can be performed n times for each block. For instance, when 128-byte writing is performed 16 times for different addresses in 2-Kbyte block and then the entire block is erased, the rewrite/erase cycle is counted as one. However, writing to the same address for several times as one erasing is not enabled (overwriting is prohibited).
Note 2. This value is based on the result of the reliability test.

Data Flash (Flash Memory for Data Storage) Characteristics (2)

Note: Items for which test conditions are not specifically stated in the table below have the same values under conditions 1 to 3.
Condition 1: VCC = PLLVCC = 2.7 to 3.6 V, VSS = PLLVSS = AVSS0 = AVSS = VREFL0 = 0 V
AVCC0 = AVCC = 3.0 to 3.6 V, VREFH0 = 3.0 V to AVCC0, VREF = 3.0 V to AVCC
Condition 2: VCC = PLLVCC = 2.7 to 3.6 V, VSS = PLLVSS = AVSS0 = AVSS = VREFL0 = 0 V
AVCC0 = AVCC = 4.0 to 5.5 V, VREFH0 = 4.0 V to AVCC0, VREF = 4.0 V to AVCC
Condition 3: VCC = PLLVCC = 4.0 to 5.5 V, VSS = PLLVSS = AVSS0 = AVSS = VREFL0 = 0 V
AVCC0 = AVCC = 4.0 to 5.5 V, VREFH0 = 4.0 V to AVCC0, VREF = 4.0 V to AVCC
Temperature range for the programming/erasure operation:
Ta = -40 to +85°C. Ta is the same under conditions 1 to 3.

Item		Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Programming time	8 bytes	t_{DP8}	—	0.4	2	ms	PCLK = 50 MHz
	128 bytes	t_{DP128}	—	1	5	ms	
Erasure time	2 Kbytes	t_{DE2K}	—	70	250	ms	PCLK = 50 MHz
Blank check time	8 bytes	t_{DBC8}	—	—	30	µs	PCLK = 50 MHz
	2 Kbytes	t_{DBC2K}	—	—	0.7	ms	
Suspend delay time during writing		t_{DSPD}	—	—	120	µs	Figure 33.24 PCLK = 50 MHz
First suspend delay time during erasing (in suspend priority mode)		t_{DSESD1}	—	—	120	µs	
Second suspend delay time during erasing (in suspend priority mode)		t_{DSESD2}	—	—	1.7	ms	
Suspend delay time during erasing (in erasure priority mode)		t_{DSEED}	—	—	1.7	ms	

- RX630 Group, RX63N Group, RX631 Group ROM (Flash Memory for Code Storage) Characteristics

Refer to Table 45.29 in RX630 Group User's Manual: Hardware Rev.1.50 and Table 50.34 in RX63N Group, RX631 Group User's Manual: Hardware Rev.1.50

Before change

ROM (Flash Memory for Code Storage) Characteristics

Conditions: VCC = AVCC0 = VREFH = VCC_USB = 2.7 to 3.6 V, VREFH0 = 2.7 V to AVCC0
VSS = AVSS0 = VREFL/VREFL0 = VSS_USB = 0 V
Temperature range for the programming/erasure operation: T_a = Topr

Item		Symbol	FCLK = 4 MHz			20 MHz ≤ FCLK ≤ 50 MHz			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	
Programming time N_{PEC} ≤ 100 hours	128 bytes	t_{P128}	—	2.8	28	—	1	10	ms
	4 Kbytes	t_{P4K}	—	63	140	—	23	50	ms
	16 Kbytes	t_{P16K}	—	252	560	—	90	200	ms
Programming time N_{PEC} > 100 hours	128 bytes	t_{P128}	—	3.4	33.6	—	1.2	12	ms
	4 Kbytes	t_{P4K}	—	75.6	168	—	27.6	60	ms
	16 Kbytes	t_{P16K}	—	302.4	672	—	108	240	ms
Erasure time N_{PEC} ≤ 100 hours	4 Kbytes	t_{E4K}	—	50	120	—	25	60	ms
	16 Kbytes	t_{E16K}	—	200	480	—	100	240	ms
Erasure time N_{PEC} > 100 hours	4 Kbytes	t_{E4K}	—	60	144	—	30	72	ms
	16 Kbytes	t_{E16K}	—	240	576	—	120	288	ms
Reprogram/erase cycle*1		N_{PEC}	1000*2	—	—	1000*2	—	—	Times
Suspend delay time during programming		t_{SPD}	—	—	400	—	—	120	µs
First suspend delay time during erasing (in suspend priority mode)		t_{SESD1}	—	—	300	—	—	120	µs
Second suspend delay time during erasing (in suspend priority mode)		t_{SESD2}	—	—	1.7	—	—	1.7	ms
Suspend delay time during erasing (in erasure priority mode)		t_{SEED}	—	—	1.7	—	—	1.7	ms
Data hold time*3		T_{DRP}	10	—	—	10	—	—	Year
FCU reset time		t_{FCUR}	35	—	—	35	—	—	µs

Note 1. Definition of reprogram/erase cycle:
The reprogram/erase cycle is the number of erasing for each block. When the reprogram/erase cycle is n times (n = 1000), erasing can be performed n times for each block. For instance, when 256-byte programming is performed 16 times for different addresses in 4-Kbyte block and then the entire block is erased, the reprogram/erase cycle is counted as one. However, programming the same address for several times as one erasing is not enabled (overwriting is prohibited).
Note 2. This indicates the minimum number that guarantees the characteristics after reprogramming. (The guaranteed value is in the range from one to the minimum number.)
Note 3. This indicates the characteristic when reprogram is performed within the specification range including the minimum number.

After change

ROM (Flash Memory for Code Storage) Characteristics (1)

Conditions: VCC = AVCC0 = VREFH = VCC_USB = 2.7 to 3.6 V, VREFH0 = 2.7 V to AVCC0
VSS = AVSS0 = VREFL/VREFL0 = VSS_USB = 0 V
Temperature range for the programming/erasure operation: T_a = Topr

Item	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Rewrite/erase cycle*1	N_{PEC}	1000	—	—	Times	
Data hold time	T_{DRP}	30*2	—	—	Year	Ta = +85°C

Note 1. Definition of reprogram/erase cycle:
The reprogram/erase cycle is the number of erasing for each block. When the reprogram/erase cycle is n times (n = 1000), erasing can be performed n times for each block. For instance, when 256-byte programming is performed 16 times for different addresses in 4-Kbyte block and then the entire block is erased, the reprogram/erase cycle is counted as one. However, programming the same address for several times as one erasing is not enabled (overwriting is prohibited).
Note 2. This value is based on the result of the reliability test.

ROM (Flash Memory for Code Storage) Characteristics (2)

Conditions: VCC = AVCC0 = VREFH = VCC_USB = 2.7 to 3.6 V, VREFH0 = 2.7 V to AVCC0
VSS = AVSS0 = VREFL/VREFL0 = VSS_USB = 0 V
Temperature range for the programming/erasure operation: T_a = Topr

Item		Symbol	FCLK = 4 MHz			20 MHz ≤ FCLK ≤ 50 MHz			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	
Programming time N_{PEC} ≤ 100 hours	128 bytes	t_{P128}	—	2.8	28	—	1	10	ms
	4 Kbytes	t_{P4K}	—	63	140	—	23	50	ms
	16 Kbytes	t_{P16K}	—	252	560	—	90	200	ms
Programming time N_{PEC} > 100 hours	128 bytes	t_{P128}	—	3.4	33.6	—	1.2	12	ms
	4 Kbytes	t_{P4K}	—	75.6	168	—	27.6	60	ms
	16 Kbytes	t_{P16K}	—	302.4	672	—	108	240	ms
Erasure time N_{PEC} ≤ 100 hours	4 Kbytes	t_{E4K}	—	50	120	—	25	60	ms
	16 Kbytes	t_{E16K}	—	200	480	—	100	240	ms
Erasure time N_{PEC} > 100 hours	4 Kbytes	t_{E4K}	—	60	144	—	30	72	ms
	16 Kbytes	t_{E16K}	—	240	576	—	120	288	ms
Suspend delay time during programming		t_{SPD}	—	—	400	—	—	120	µs
First suspend delay time during erasing (in suspend priority mode)		t_{SESD1}	—	—	300	—	—	120	µs
Second suspend delay time during erasing (in suspend priority mode)		t_{SESD2}	—	—	1.7	—	—	1.7	ms
Suspend delay time during erasing (in erasure priority mode)		t_{SEED}	—	—	1.7	—	—	1.7	ms
FCU reset time		t_{FCUR}	35	—	—	35	—	—	µs

- RX630 Group, RX63N Group, RX631 Group E^2 Flash Characteristics

  Refer to Table 45.30 in RX630 Group User's Manual: Hardware Rev.1.50 and Table 50.35 in RX63N Group, RX631 Group User's Manual: Hardware Rev.1.50

Before change

E2 Flash Characteristics

Conditions: VCC = AVCC0 = VREFH = VCC_USB = 2.7 to 3.6 V, VREFH0 = 2.7 V to AVCC0
VSS = AVSS0 = VREFL/VREFL0 = VSS_USB = 0 V
Temperature range for the programming/erasure operation: Ta = Topr

Item		Symbol	FCLK = 4 MHz			20 MHz ≤ FCLK ≤ 50 MHz			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	
Programming time N_{PEC} ≤ 100 hours	2 bytes	t_{DP2}	—	0.7	6	—	0.25	2	ms
Programming time N_{PEC} > 100 hours	2 bytes	t_{DP2}	—	0.7	6	—	0.25	2	ms
Erasure time N_{PEC} ≤ 100 hours	32 bytes	t_{DE32}	—	4	40	—	2	20	ms
Erasure time N_{PEC} > 100 hours	32 bytes	t_{DE32}	—	7	40	—	4	20	ms
Blank check time	2 bytes	t_{DBC2}	—	—	100	—	—	30	µs
Reprogram/erase cycle[*1]		N_{DPEC}	100000 [*2]	—	—	100000 [*2]	—	—	Times
Suspend delay time during programming		t_{DSPD}	—	—	250	—	—	120	µs
First suspend delay time during erasing (in suspend priority mode)		t_{DSESD1}	—	—	250	—	—	120	µs
Second suspend delay time during erasing (in suspend priority mode)		t_{DSESD2}	—	—	500	—	—	300	µs
Suspend delay time during erasing (in erasure priority mode)		t_{DSEED}	—	—	500	—	—	300	µs
Data hold time[*3]		T_{DDRP}	10	—	—	10	—	—	Year

Note 1. Definition of reprogram/erase cycle:
The reprogram/erase cycle is the number of erasing for each block. When the reprogram/erase cycle is n times (n = 100000), erasing can be performed n times for each block. For instance, when 128-byte programming is performed 16 times for different addresses in 2-Kbyte block and then the entire block is erased, the reprogram/erase cycle is counted as one. However, programming the same address for several times as one erasing is not enabled (overwriting is prohibited).

Note 2. This indicates the minimum number that guarantees the characteristics after reprogramming. (The guaranteed value is in the range from one to the minimum number.)

Note 3. This indicates the characteristic when reprogram is performed within the specification range including the minimum number.

After change

E2 Flash Characteristics (1)

Conditions: VCC = AVCC0 = VREFH = VCC_USB = 2.7 to 3.6 V, VREFH0 = 2.7 V to AVCC0
VSS = AVSS0 = VREFL/VREFL0 = VSS_USB = 0 V
Temperature range for the programming/erasure operation: Ta = Topr

Item	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Reprogram/erase cycle*1	N_{DPEC}	100000	—	—	Times	
Data hold time	T_{DDRP}	30*2	—	—	Year	T_a = +85°C

Note 1. Definition of reprogram/erase cycle:
The reprogram/erase cycle is the number of erasing for each block. When the reprogram/erase cycle is n times (n = 100000), erasing can be performed n times for each block. For instance, when 128-byte programming is performed 16 times for different addresses in 2-Kbyte block and then the entire block is erased, the reprogram/erase cycle is counted as one. However, programming the same address for several times as one erasing is not enabled (overwriting is prohibited).
Note 2. This value is based on the result of the reliability test.

E2 Flash Characteristics (2)

Conditions: VCC = AVCC0 = VREFH = VCC_USB = 2.7 to 3.6 V, VREFH0 = 2.7 V to AVCC0
VSS = AVSS0 = VREFL/VREFL0 = VSS_USB = 0 V
Temperature range for the programming/erasure operation: Ta = Topr

Item		Symbol	FCLK = 4 MHz			20 MHz ≤ FCLK ≤ 50 MHz			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	
Programming time N_{DPEC} ≤ 100 hours	2 bytes	t_{DP2}	—	0.7	6	—	0.25	2	ms
Programming time N_{DPEC} > 100 hours	2 bytes	t_{DP2}	—	0.7	6	—	0.25	2	ms
Erasure time N_{DPEC} ≤ 100 hours	32 bytes	t_{DE32}	—	4	40	—	2	20	ms
Erasure time N_{DPEC} > 100 hours	32 bytes	t_{DE32}	—	7	40	—	4	20	ms
Blank check time	2 bytes	t_{DBC2}	—	—	100	—	—	30	µs
Suspend delay time during programming		t_{DSPD}	—	—	250	—	—	120	µs
First suspend delay time during erasing (in suspend priority mode)		t_{DSESD1}	—	—	250	—	—	120	µs
Second suspend delay time during erasing (in suspend priority mode)		t_{DSESD2}	—	—	500	—	—	300	µs
Suspend delay time during erasing (in erasure priority mode)		t_{DSEED}	—	—	500	—	—	300	µs